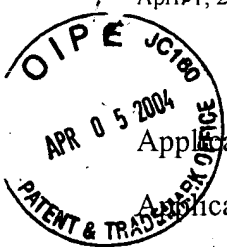


*Inge*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant: Jagdish Narayan  
Application No.: 10/608,780 Group Art Unit: 2811  
Filed: June 27, 2003 Examiner: Not assigned  
Confirmation No.: 8117  
Title: DOMAIN EPITAXY FOR THIN FILM GROWTH

CERTIFICATE OF MAILING OR TRANSMISSION	
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, or is being facsimile transmitted to the United States Patent and Trademark Office on:	
<u>April 1, 2004</u> Date	<u><i>Shannon Lewis</i></u> Signature
<u>Shannon Lewis</u> Typed or printed name of person signing certificate	

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This Information Disclosure Statement is submitted:

- ☐ under 37 CFR 1.129(a), or  
(First/Second submission after Final Rejection)
- ☒ under 37 CFR 1.97(b), or  
(Within any one of the following time periods: three months of filing national application (other than a CPA) or date of entry of the national stage in an international application; or before the mailing date of a first office action on the merits in a non-provisional application, including a CPA, or a Request for Continued Examination).
- ☐ under 37 CFR 1.97(c) together with either:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, or
- ☐ a \$180.00 fee under 37 CFR 1.17(p), or  
(After the 37 CFR 1.97(b) time period, but before final action or notice of allowance, whichever occurs first)
- ☐ under 37 CFR 1.97(d) together with:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, and
- ☐ a \$180.00 fee under 37 CFR 1.17(p), or  
(Filed after final action or notice of allowance, whichever occurs first, but on or before payment of the issue fee)
- ☐ under 37 CFR 1.97(i):  
Applicant requests that the IDS and cited reference(s) be placed in the application filewrapper.  
(Filed after payment of issue fee)

Statement Under 37 CFR 1.97(e)

- ☐ Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement; or
- ☐ No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

Statement Under 37 CFR 1.704(d) (Patent Term Adjustment)

Applies to original applications (other than design) filed on or after May 29, 2000

- ☐ Each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in § 1.56(c) more than thirty days prior to the filing of the Information Disclosure Statement.
- ☒ Enclosed herewith is form PTO-1449:
- ☒ Copies of the cited references AA-AB8, AL-AO6 and AR-AU6 are enclosed.
- ☐ Since this application was filed after June 30, 2003, copies of issued U.S. patents and published U.S. applications are not required and are not being provided.
- ☐ Copies of the cited references are enclosed except those entered in prior application, U.S. Application No. [ ], to which priority under 35 U.S.C. 120 is claimed. [The earlier application contains copies of the cited references.]
- ☐ The listed references were cited in the enclosed International Search Report in a counterpart foreign application.
- ☒ The "concise explanation" requirement (non-English references) for references AM, AN, AO, AP, AS, AL2, AN2, AP2, AQ2, AN3, AO3, AP3, AQ3, AL4, AM4, AN4, AO4, AP4, AQ4, AL5, AM5, AN5 and AN6 under 37 CFR 1.98(a)(3) is satisfied by:
- ☐ the explanation provided on the attached sheet.
- ☐ the explanation provided in the Specification.
- ☐ submission of the enclosed International Search Report.
- ☐ submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.
- ☒ the enclosed English language abstracts.

[ X ] Applicant requests that the following non-published pending applications be considered:

Examiner's  
Initials

\_\_\_\_\_ U.S. Patent Application No. 10/463,219, by John C. C. Fan, Hong K. Choi, Tchang-Hun Oh, Jyh Chia Chen and Jagdish Narayan, filed June 17, 2003, Docket No.: 0717.2032-001

\_\_\_\_\_ U.S. Patent Application No. [    ], by [inventor(s)], filed [    ], Docket No.: [    ]

\_\_\_\_\_ U.S. Patent Application No. [    ], by [inventor(s)], filed [    ], Docket No.: [    ]

\_\_\_\_\_  
Examiner

\_\_\_\_\_  
Date

[ X ] A copy of the above-cited application, including the current claims, is enclosed.

[    ] A copy of each above-cited application, including the current claims, is enclosed, except those entered in prior application, U.S. Application No. [    ], to which priority under 35 U.S.C. 120 is claimed.

The Examiner is requested to return a copy of the above list of pending applications indicating which references were considered with the next office communication.

It is requested that the information disclosed herein be made of record in this application.

Method of payment:

[    ] A check for the fee noted above is enclosed, or the fee has been included in the check with the accompanying Reply. A copy of this Statement is enclosed.

[    ] Please charge Deposit Account 08-0380 in the amount of \$[    ]. A copy of this Statement is enclosed.

[X] Please charge any deficiency in fees and credit any overpayment to Deposit Account 08-0380.

Respectfully submitted,

HAMILTON, BROOK, SMITH & REYNOLDS, P.C.

By \_\_\_\_\_

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Concord, MA 01742-9133

Dated: 7/1/04

PTC-1449 REPRODUCED

ATTORNEY DOCKET NO.  
0717.2033-002APPLICATION NO.  
10/608,780INFORMATION DISCLOSURE CITATION  
IN AN APPLICATIONFIRST NAMED INVENTOR  
Jagdish NarayanFILING DATE  
June 27, 2003

March 24, 2004

EXAMINER  
Not yet assignedCONFIRMATION NO.  
8117GROUP  
2811

(Use several sheets if necessary)

## U.S. PATENT DOCUMENTS

EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
	AA	4,153,905	05-08-1979	Charmakadze <i>et al.</i>
	AB	4,495,514	01-22-1985	Lawrence <i>et al.</i>
	AC	4,670,088	06-02-1987	Tsaur <i>et al.</i>
	AD	4,946,548	08-07-1990	Kotaki <i>et al.</i>
	AE	4,966,862	10-30-1990	Edmond
	AF	5,091,333	02-25-1992	Fan <i>et al.</i>
	AG	5,210,051	05-11-1993	Carter, Jr.
	AH	5,239,188	08-24-1993	Takeuchi <i>et al.</i>
	AI	5,247,533	09-21-1993	Okazaki <i>et al.</i>
	AJ	5,272,108	12-21-1993	Kozawa
	AK	5,278,433	01-11-1994	Manabe <i>et al.</i>
	AA2	5,281,830	01-25-1994	Kotaki <i>et al.</i>
	AB2	5,285,078	02-08-1994	Mimura <i>et al.</i>
	AC2	5,290,393	03-01-1994	Nakamura
	AD2	5,306,662	04-26-1994	Nakamura <i>et al.</i>
	AE2	5,323,022	06-21-1994	Glass <i>et al.</i>
	AF2	5,334,277	08-02-1994	Nakamura
	AG2	5,369,289	11-29-1994	Tamaki <i>et al.</i>
	AH2	5,385,862	01-31-1995	Moustakas
	AI2	5,406,123	04-11-1995	Narayan
	AJ2	5,408,120	04-18-1995	Manabe, <i>et al.</i>
	AK2	5,433,169	07-18-1995	Nakamura
	AA3	5,468,678	11-21-1995	Nakamura <i>et al.</i>
	AB3	5,578,839	11-26-1996	Nakamura, <i>et al.</i>
	AC3	5,563,422	10-08-1996	Nakamura, <i>et al.</i>
	AD3	5,652,434	07-29-1997	Nakamura, <i>et al.</i>

EXAMINER

DATE CONSIDERED

PTO:1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned		CONFIRMATION NO. 8117	GROUP 2811

## U.S. PATENT DOCUMENTS

EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
	AE3	5,686,738	11-11-1997	Moustakas
	AF3	5,733,796	03-31-1998	Manabe <i>et al.</i>
	AG3	5,734,182	03-31-1998	Nakamura <i>et al.</i>
	AH3	5,747,832	05-05-1998	Nakamura <i>et al.</i>
	AI3	5,751,752	05-12-1998	Shakuda
	AJ3	5,767,581	06-16-1998	Nakamura <i>et al.</i>
	AK3	5,777,350	07-07-1998	Nakamura <i>et al.</i>
	AA4	5,828,684	10-27-1998	Van de Walle
	AB4	5,850,410	12-15-1998	Kuramata
	AC4	5,877,558	03-02-1999	Nakamura <i>et al.</i>
	AD4	5,880,486	03-09-1999	Nakamura <i>et al.</i>
	AE4	5,905,276	05-18-1999	Manabe <i>et al.</i>
	AF4	5,959,307	09-28-1999	Nakamura <i>et al.</i>
	AG4	5,998,925	12-07-1999	Shimizu <i>et al.</i>
	AH4	6,017,774	01-25-2000	Yuasa, <i>et al.</i>
	AI4	6,051,849	04-18-2000	Davis <i>et al.</i>
	AJ4	6,066,861	05-23-2000	Höhn <i>et al.</i>
	AK4	6,069,440	05-30-2000	Shimizu <i>et al.</i>
	AA5	6,078,063	06-20-2000	Nakamura <i>et al.</i>
	AB5	6,084,899	07-04-2000	Shakuda
	AC5	6,093,965	07-25-2000	Nakamura <i>et al.</i>
	AD5	6,115,399	09-05-2000	Shakuda
	AE5	6,153,010	11-28-2000	Kiyoku <i>et al.</i>
	AF5	6,172,382 B1	01-09-2001	Nagahama <i>et al.</i>
	AG5	6,204,512 B1	03-20-2001	Nakamura <i>et al.</i>
	AH5	6,215,133 B1	04-10-2001	Nakamura <i>et al.</i>

EXAMINER	DATE CONSIDERED
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PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned	CONFIRMATION NO. 8117	GROUP 2811	

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EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
	AI5	6,245,259 B1	06-12-2001	Höhn <i>et al.</i>
	AJ5	6,249,012 B1	06-19-2001	Manabe <i>et al.</i>
	AK5	6,337,493 B1	01-08-2002	Tanizawa <i>et al.</i>
	AA6	6,362,017 B1	03-26-2002	Manabe <i>et al.</i>
	AB6	US 2001/0022367 A1	09-20-2001	Nakamura <i>et al.</i>
	AC6	US 2001/0030318 A1	10-18-2001	Nakamura <i>et al.</i>
	AD6	US 2002/0046693 A1	04-25-2002	Kiyoku <i>et al.</i>
	AE6	US 2002/0060326 A1	05-23-2002	Manabe <i>et al.</i>
	AF6	US 2003/0199171 A1	10-23-2003	Rice <i>et al.</i>
	AG6	US 2003/0160246 A1	08-28-2003	Narayan <i>et al.</i>
	AH6	US 2001/0028062 A1	10-11-2001	Uemura <i>et al.</i>
	AI6	US 2003/0222263 A1	12-04-2003	Choi
	AJ6	US 2004/0000672 A1	01-01-2004	Fan <i>et al.</i>
	AK6	US 2004/0000671 A1	01-01-2004	Oh <i>et al.</i>
	AA7	US 2004/0000670 A1	01-01-2004	Oh <i>et al.</i>
	AB7	US 2001/0050375 A1	12-13-2001	Van Dalen
	AC7	5,383,088	01-17-1995	Chapple-Sokol <i>et al.</i>
	AD7	6,287,947 B1	09-11-2001	Ludowise <i>et al.</i>
	AE7	6,475,854 B2	11-05-2002	Narwankar <i>et al.</i>
	AF7	6,255,129 B1	07-03-2001	Lin
	AG7	6,097,040	08-01-2000	Morimoto <i>et al.</i>
	AH7	6,067,222	05-23-2000	Hausmann
	AI7	4,625,182	11-25-1986	Bovino <i>et al.</i>
	AJ7	6,241,344 B1	06-05-2001	Machida
	AK7	5,516,731	05-14-1996	Toutouchi <i>et al.</i>
	AA8	5,834,326	11-10-1998	Miyachi <i>et al.</i>

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EXAMINER	DATE CONSIDERED
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PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned		CONFIRMATION NO. 8117	GROUP 2811

FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER Country Code-Number-Kind Code (if known)	DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT	TRANSLATION YES NO
	AL	JP9167857 (abstract only)	06-24-1997	Toshiba Corp	
	AM	JP 52/028887	03-04-1977	Fujitsu LTD	X
	AN	JP 05-243614	09-21-1993	Sharp Corp	X
	AO	JP 4236478	08-25-1992	Pioneer Electron Corp	X
	AP	JP 03-218625	09-26-1991	Univ Nagoya	X
	AQ	JP 03-252177 (abstract only)	11-11-1991	Toyoda Gosei Co LTD Toyoda Central Res & Dev Lab Univ Nagoya Res Dev Corp of Japan	
	AL2	JP 54-093380	07-24-1979	Fujitsu LTD	X
	AM2	JP 9092880 (abstract only)	04-04-1997	Toyoda Gosei Co LTD	
	AN2	JP 8213692	08-20-1996	Hitachi LTD	X
	AO2	JP 11145513 (abstract only)	05-28-1999	Sharp Corp	
	AP2	JP 04-068579	03-04-1992	Sharp Corp	X
	AQ2	JP 02-229475	09-12-1990	Nippon Telegr & Teleph Corp	X
	AL3	JP 04-242985 (abstract only)	08-31-1992	Toyoda Gosei Co LTD Akasaki Isamu Amano Hiroshi	
	AM3	JP9134881 (abstract only)	05-20-1997	Matsushita Electron Corp	
	AN3	JP 59-228776	12-22-1984	Nippon Telegr & Teleph Corp	X
	AO3	JP 06-177423	06-24-1994	Nichia Chem Ind LTD	X
	AP3	JP 06-268259	09-22-1994	Nichia Chem Ind LTD	X
	AQ3	JP 02-229475	09-12-1990	Nippon Telegr & Teleph Corp	X
	AL4	JP 2229475	09-12-1990	Nippon Telegr & Teleph Corp	X
	AM4	JP 06-021511	01-28-1994	Nippon Telegr & Teleph Corp	X
	AN4	JP 4209577	07-30-1992	Nippon Telegr & Teleph Corp	X
	AO4	JP 61-056474	03-22-1986	Matsushita Electric Ind Co LTD	X
	AP4	JP 8167735	06-25-1996	Hitachi Cable LTD	X

EXAMINER	DATE CONSIDERED
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(Use several sheets if necessary)

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PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned		CONFIRMATION NO. 8117	GROUP 2811

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AR	Foresi, J.S. and Moustakas, T.D., "Metal contacts to gallium nitride," <i>Appl. Phys. Lett.</i> 62(22):2859-2861 (1993).	
AS	Nakamura, S., "InGaN blue - light - emitting diodes," <i>Journal of the Institute of Electronics, Information and Communication Engineers</i> 76(9):913-917 (1993) (Abstract).	
AT	Akasaki, I. and Amano, H., "High efficiency UV and blue emitting devices prepared by MOVPE and low energy electron beam irradiation treatment," <i>Physical Concepts of Materials for Novel Optoelectronic Device Applications</i> , 1361:138-149 (1990).	
AU	Amano, H., <i>et al.</i> , "P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEBI)," <i>Japanese Journal of Applied Physics</i> 28(12):L2112-L2114 (1989).	
AV	Andreev, V.M., <i>et al.</i> , "Luminescence Properties of i-n, i-n-i and n-i-n Structures Made of Epitaxial Layers GaN/ $\alpha$ -Al <sub>2</sub> O <sub>3</sub> ," <i>Journal of Luminescence</i> 35:9-16 (1986).	
AW	Boulou, M., <i>et al.</i> , "Recombination Mechanisms in GaN:Zn," <i>Journal of Luminescence</i> 18/19:767-770 (1979).	
AX	Casey, Jr., H.C. and Panish, M.B., "SLAB-Dielectric Waveguides," in <i>Heterostructure Lasers</i> , (NY: Academic Press), pp. 32-35 (1978).	
AY	Goldenberg, B., <i>et al.</i> , "Ultraviolet and violet light-emitting GaN diodes grown by low-pressure metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> 62(4):381-383 (1993).	
AZ	F. Goodenough, "Exotic Semiconductors Showcased at the IEDM," <i>Electronic Design</i> , pp. 60, 62, 64-66, 68 (1994).	
AR2	Hayashi, I., <i>et al.</i> , "Junction Lasers Which Operate Continuously at Room Temperature," <i>Appl. Phys. Lett.</i> 17(3):109-111 (1970).	
AS2	Jacob, G., <i>et al.</i> , "GaN Electroluminescent Devices: Preparation and Studies," <i>Journal of Luminescence</i> 17:263-282 (1978).	
AT2	Jang, J.-S., <i>et al.</i> , "High Quality Non-Alloyed Pt Ohmic Contacts to P-Type GaN Using Two-Step Surface Treatment," <i>MRS Internet J. Nitride Semiconductor Res.</i> F99W10.4 .	
AU2	Kaminska, E., <i>et al.</i> , "Ni/Si-Based Contacts to GaN: Thermally Activated Structural Transformations Leading to Ohmic Behavior," <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G9.9.	

EXAMINER	DATE CONSIDERED
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PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned	CONFIRMATION NO. 8117	GROUP 2811	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	AV2	Kampen, T.U. and Mönch, W., "Metal Contacts on a-GaN," <i>MRS Internet J. Nitride Semicond. Res.</i> 1(41).
	AW2	Madar, R., "High Pressure Solution Growth of GaN <sup>+</sup> ," <i>Journal of Crystal Growth</i> 31:197-203 (1975).
	AX2	Matsuoka, T., "Growth and Properties of a Wide-Gap Semiconductor InGaN," <i>Optoelectronics</i> 5(1):53-64 (1990).
	AY2	T. Matsuoka, "Current status of GaN and related compounds as wide-gap semiconductors," <i>Journal of Crystal Growth</i> 124:433-438 (1992).
	AZ2	Nakamura, S., <i>et al.</i> , "High-power InGaN/GaN double-heterostructure violet light emitting diodes," <i>Appl. Phys. Lett.</i> 62(19):2390-2392 (1993).
	AR3	Nakamura, S., <i>et al.</i> , "P-GaN/N-InGaN/N-GaN Double-Heterostructure Blue-Light-Emitting Diodes," <i>Jpn. J. Appl. Phys.</i> 32:L8-L11 (1993).
	AS3	S. Nakamura, "Growth of In <sub>x</sub> Ga <sub>(1-x)</sub> N compound semiconductors and high-power InGaN/AlGaN double heterostructure violet-light-emitting diodes," <i>Microelectronics Journal</i> 25:651-659 (1994).
	AT3	Nakamura, S., <i>et al.</i> , "High-Power GaN P-N Junction Blue-Light-Emitting Diodes," <i>Japanese Journal of Applied Physics</i> 30(12A):L1998-L2001 (1991).
	AU3	Nakamura, S., "InGaN/AlGaN Double-Heterostructure Blue LEDs," <i>Mat. Res. Soc. Symp. Proc. Vol.</i> 339:173-178 (1994).
	AV3	Nakamura, S., <i>et al.</i> , "Thermal Annealing Effects on P-Type Mg-Doped GaN Films," <i>Jpn. J. Appl. Phys.</i> 31:L139-L142 (1992).
	AW3	Nakamura, S., "Zn-doped InGaN growth and InGaN/AlGaN double-heterostructure blue-light-emitting diodes," <i>Journal of Crystal Growth</i> 145:911-917 (1994).
	AX3	Nakamura, S., <i>et al.</i> , "High-brightness InGaN/AlGaN double-heterostructure blue-green-light-emitting diodes," <i>J. Appl. Phys.</i> 76(12):8189-8191 (1994).
	AY3	Nakamura, S., <i>et al.</i> , "Cd-Doped InGaN Films Grown on GaN Films," <i>Jpn. J. Appl. Phys.</i> 32:L338-L341 (1993).

EXAMINER	DATE CONSIDERED
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RTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned		CONFIRMATION NO. 8117	GROUP 2811

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AZ3	Nakamura, S., "High-Power InGaN/AlGa <sub>N</sub> Double-Heterostructure Blue-Light-Emitting Diodes," Int'l Electronic Devices Meeting 94:567-570 (1994).	
AR4	Piotrowska, A., <i>et al.</i> , "Ohmic Contacts to III-V Compound Semiconductors: A Review of Fabrication Techniques," <i>Solid-State Electronics</i> 26(3):179-197 (1983).	
AS4	Sporken, R., <i>et al.</i> , "XPS study of Au/GaN and Pt/GaN contacts," <i>MRS Internet J. Nitride Semiconductor Res.</i> 2(23)(1997).	
AT4	Venugopalan, H.S., <i>et al.</i> , "Phase Formation and Morphology in Nickel and Nickel/Gold Contacts To Gallium Nitride," <i>MRS Internet Journal Nitride Semiconductor Research</i> (1997) <URL:http://nsr.mij.mrs.org/MRS/S97-D/4.10>.	
AU4	Zhou, L., <i>et al.</i> , "Characteristics of Ti/Pt/Au Ohmic Contacts on <i>p</i> -type GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N Superlattices," <i>MRS Internet J. Nitride Semicond. Res.</i> F99W10.3.	
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RTQ-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>March 24, 2004</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Not yet assigned	CONFIRMATION NO. 8117	GROUP 2811	

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